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Kind regards,

Team Nexperia



PBSS5330PA

30 V, 3 A PNP low V_{CEsat} (BISS) transistor

7 April 2015

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor, encapsulated in an ultra thin SOT1061 leadless small Surface-Mounted Device (SMD) plastic package with medium power capability.

NPN complement: PBSS4330PA.

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- Exposed heat sink for excellent thermal and electrical conductivity
- Leadless small SMD plastic package with medium power capability

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-30	V
I _C	collector current		-	-	-3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-5	A
R _{CEsat}	collector-emitter saturation resistance	I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	75	107	mΩ

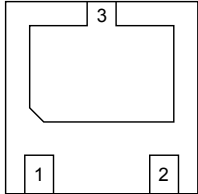
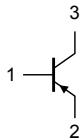


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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	B	base	 <p>Transparent top view DFN2020-3 (SOT1061)</p>	 <p>sym013</p>
2	E	emitter		
3	C	collector		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS5330PA	DFN2020-3	DFN2020-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 x 2 x 0.65 mm	SOT1061

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5330PA	AJ

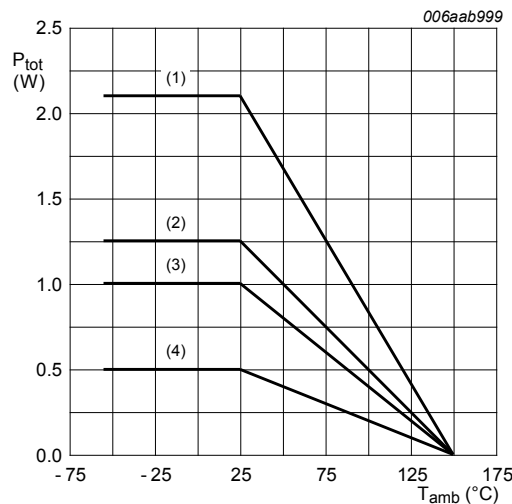
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-30	V
V_{CEO}	collector-emitter voltage	open base		-	-30	V
V_{EBO}	emitter-base voltage	open collector		-	-6	V
I_C	collector current			-	-3	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms		-	-5	A
I_B	base current			-	-500	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	500	mW
			[2]	-	1	W
			[3]	-	1.25	W
			[4]	-	2.1	W
T_j	junction temperature			-	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, mounting pad for collector 1 cm²
- (4) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	250	K/W
			[2]	-	-	125	K/W
			[3]	-	-	100	K/W
			[4]	-	-	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

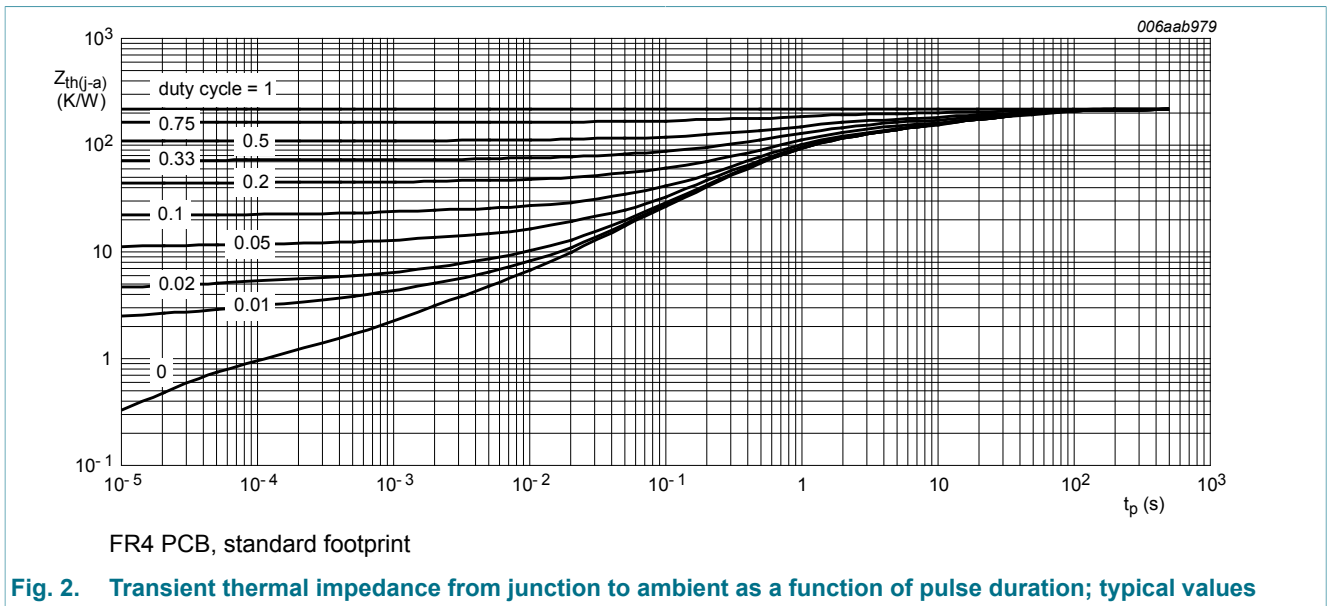
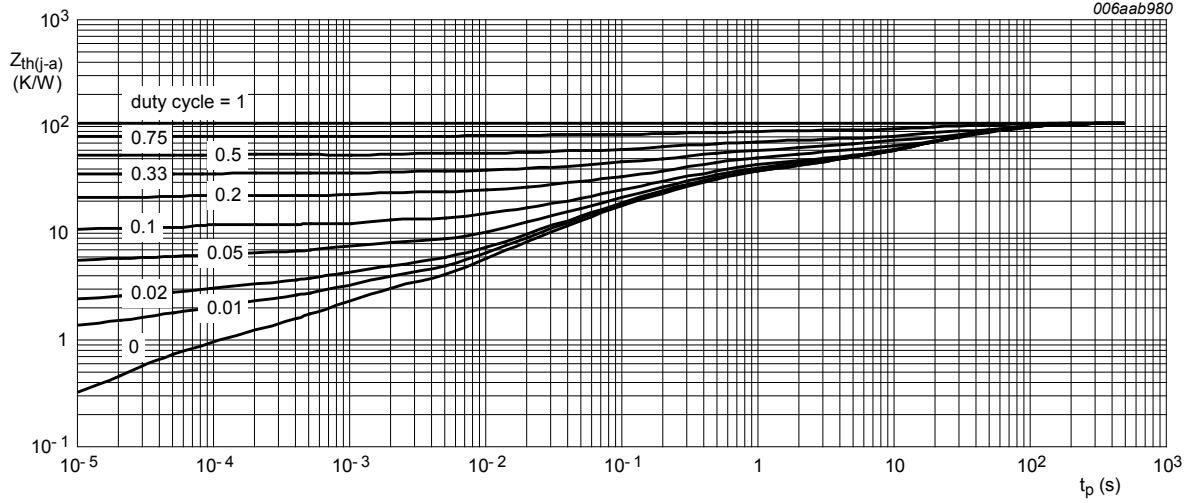
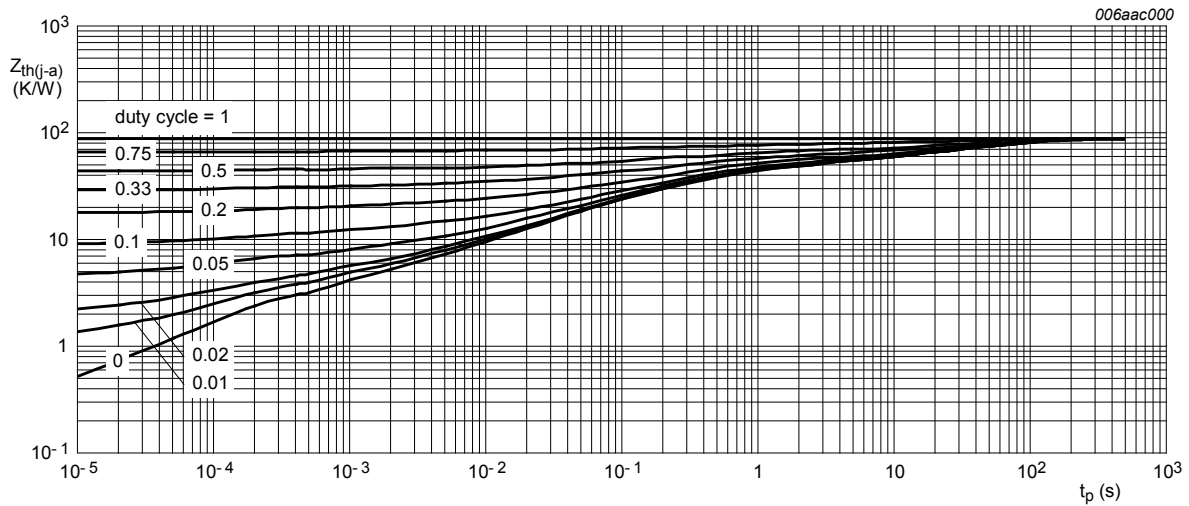


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



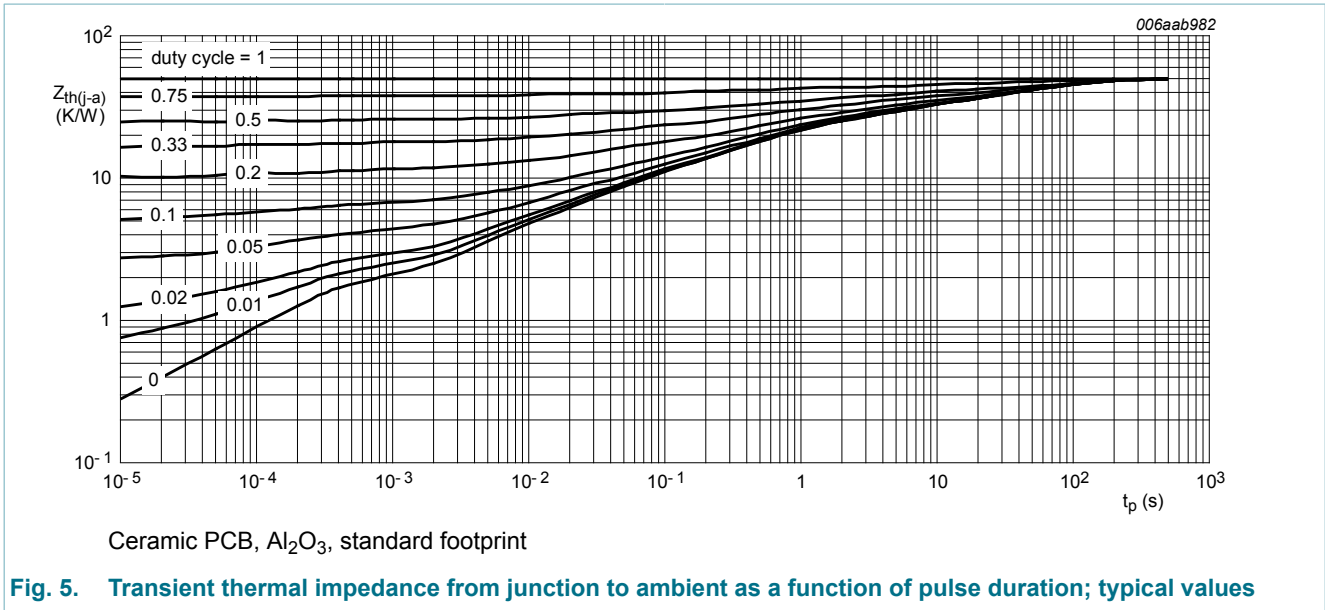
FR4 PCB, mounting pad for collector 1 cm²

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

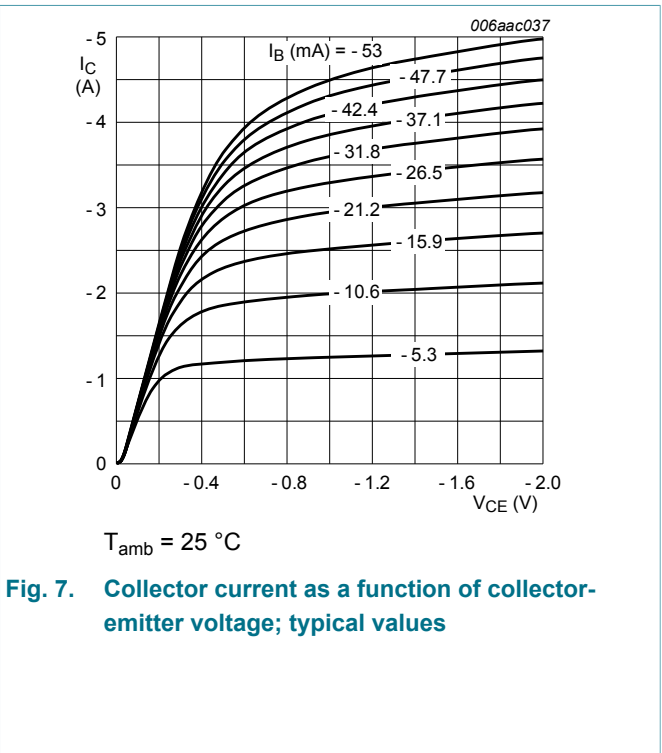
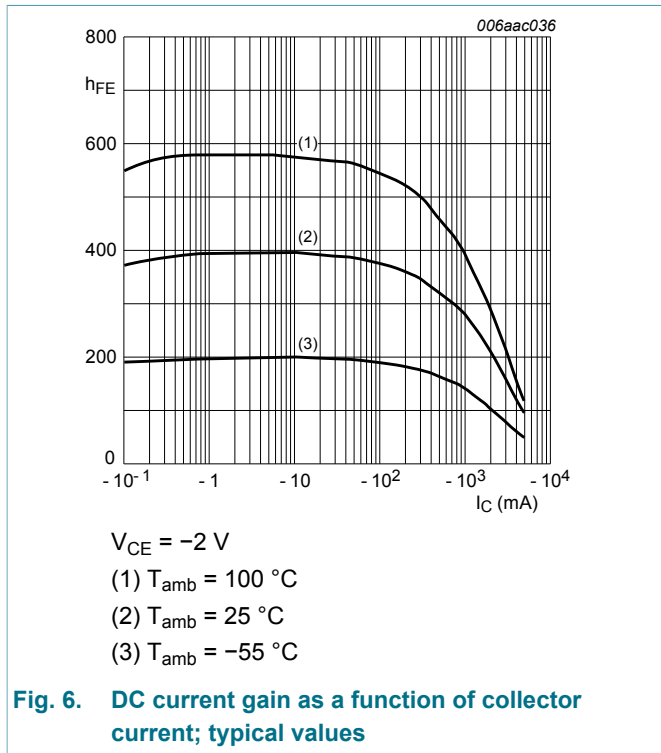


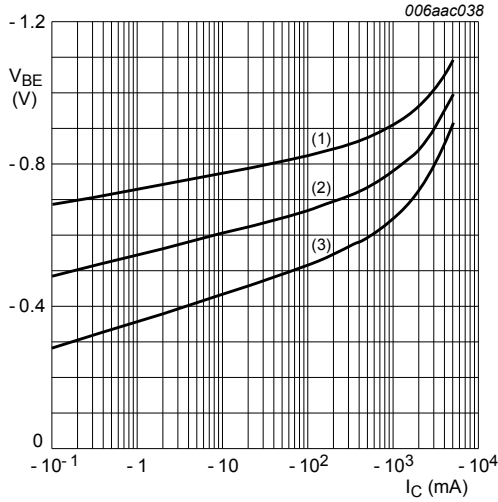
10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
		V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -24 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -0.5 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	200	320	-	
		V _{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	175	280	450	
		V _{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	140	210	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	100	160	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -0.5 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-45	-70	mV
		I _C = -1 A; I _B = -50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-90	-130	mV
		I _C = -2 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-170	-240	mV
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-230	-320	mV
R _{CEsat}	collector-emitter saturation resistance	t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	75	107	mΩ
V _{BEsat}	base-emitter saturation voltage	I _C = -2 A; I _B = -100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.89	-1.1	V
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.97	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V _{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02 ; T _{amb} = 25 °C	-	-0.75	-1	V
t _d	delay time	V _{CC} = -9 V; I _C = -2 A; I _{Bon} = -0.1 A; I _{Boff} = 0.1 A; T _{amb} = 25 °C	-	11	-	ns
t _r	rise time		-	59	-	ns
t _{on}	turn-on time		-	70	-	ns
t _s	storage time		-	165	-	ns
t _f	fall time		-	35	-	ns
t _{off}	turn-off time		-	200	-	ns

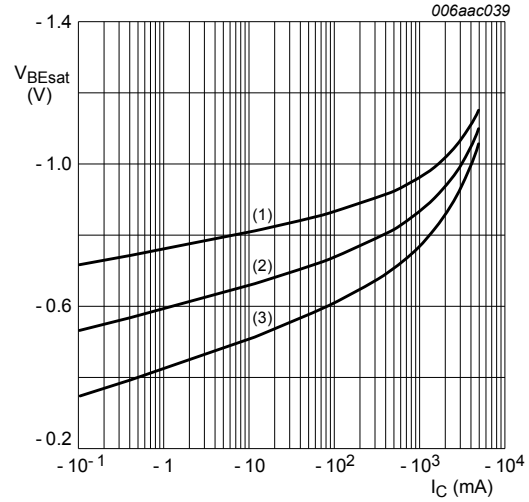
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_T	transition frequency	$V_{CE} = -5\text{ V}$; $I_C = -100\text{ mA}$; $f = 100\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	100	165	-	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}$; $I_E = 0\text{ A}$; $i_e = 0\text{ A}$; $f = 1\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	-	38	45	pF





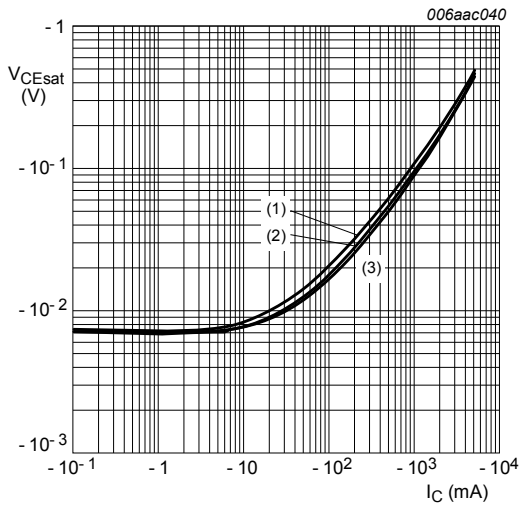
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 8. Base-emitter voltage as a function of collector current; typical values



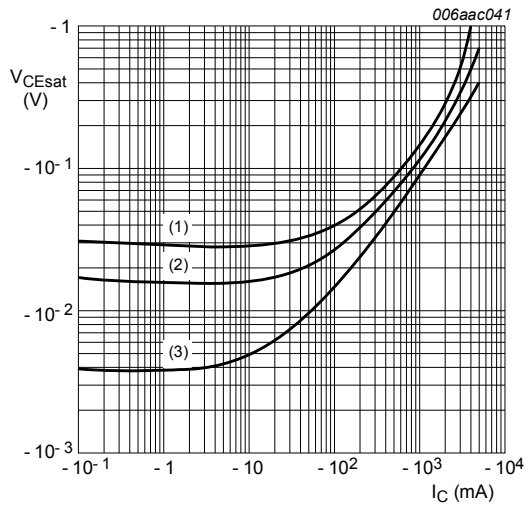
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig. 9. Base-emitter saturation voltage as a function of collector current; typical values



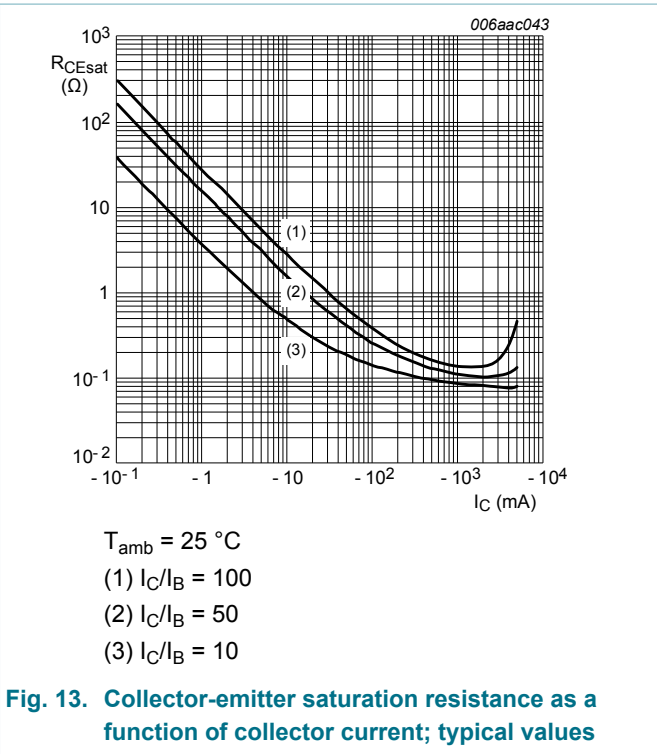
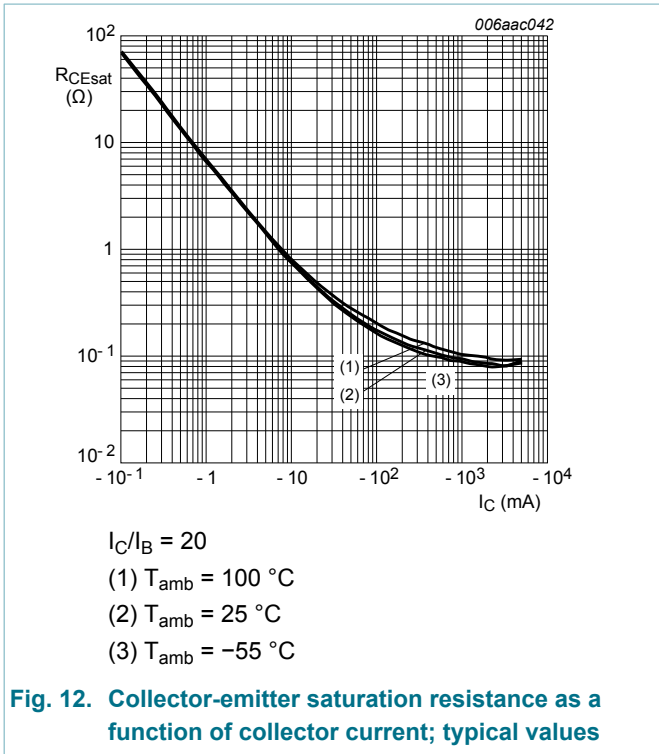
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig. 10. Collector-emitter saturation voltage as a function of collector current; typical values



$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



11. Test information

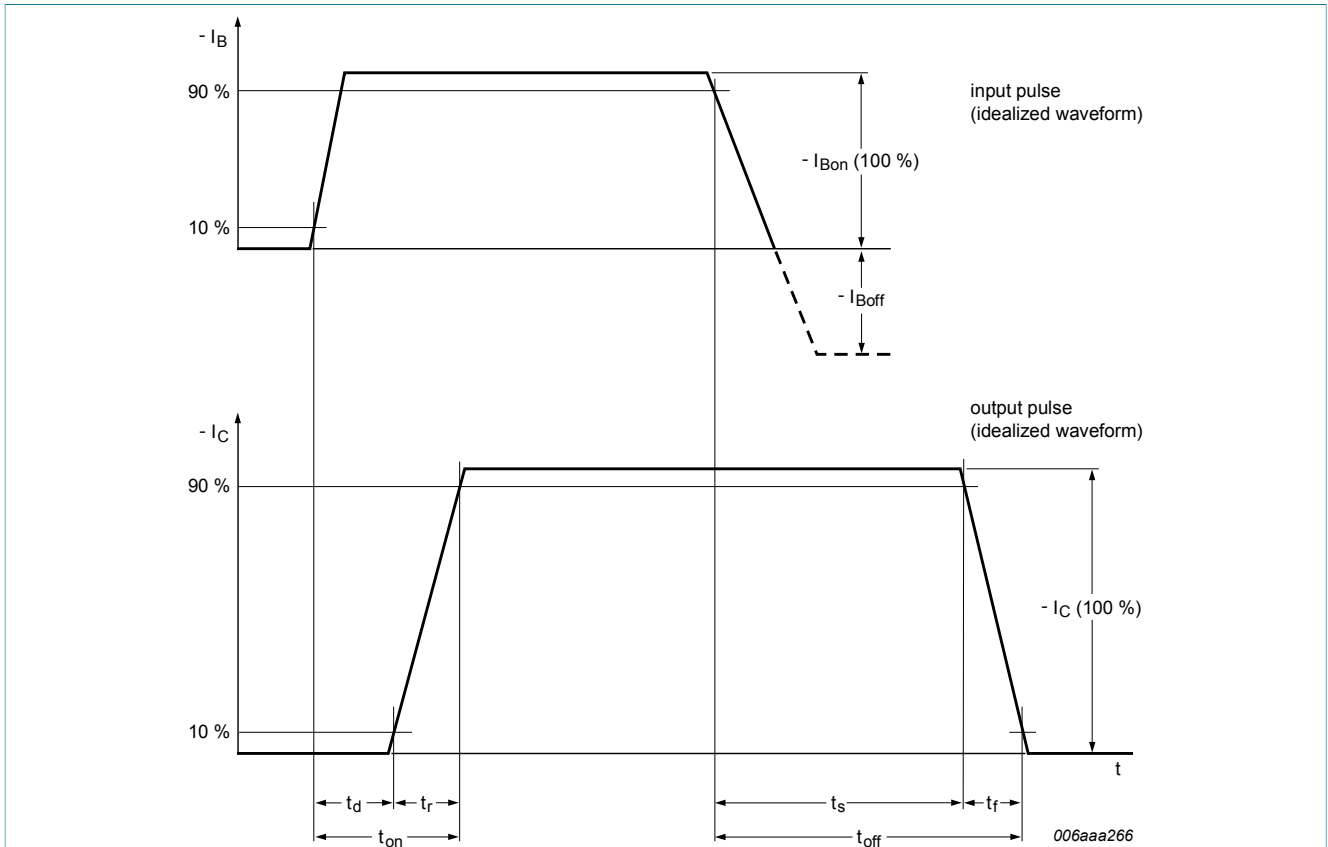


Fig. 14. BISS transistor switching time definition

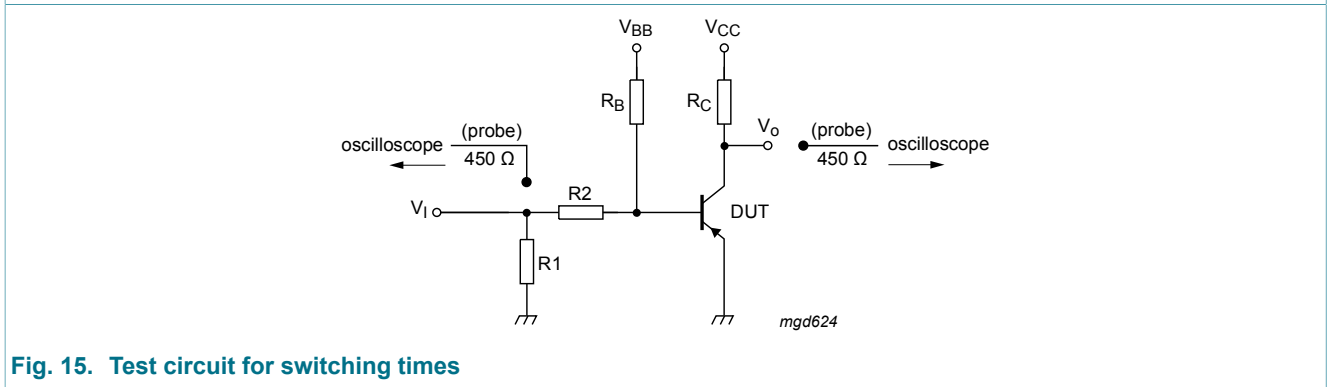


Fig. 15. Test circuit for switching times

12. Package outline

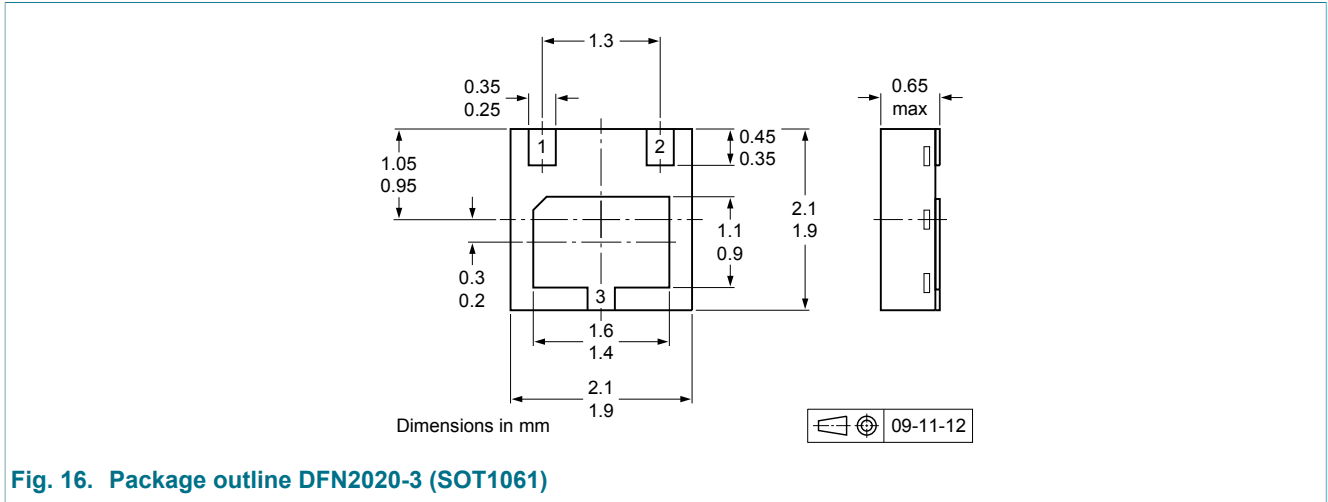


Fig. 16. Package outline DFN2020-3 (SOT1061)

13. Soldering

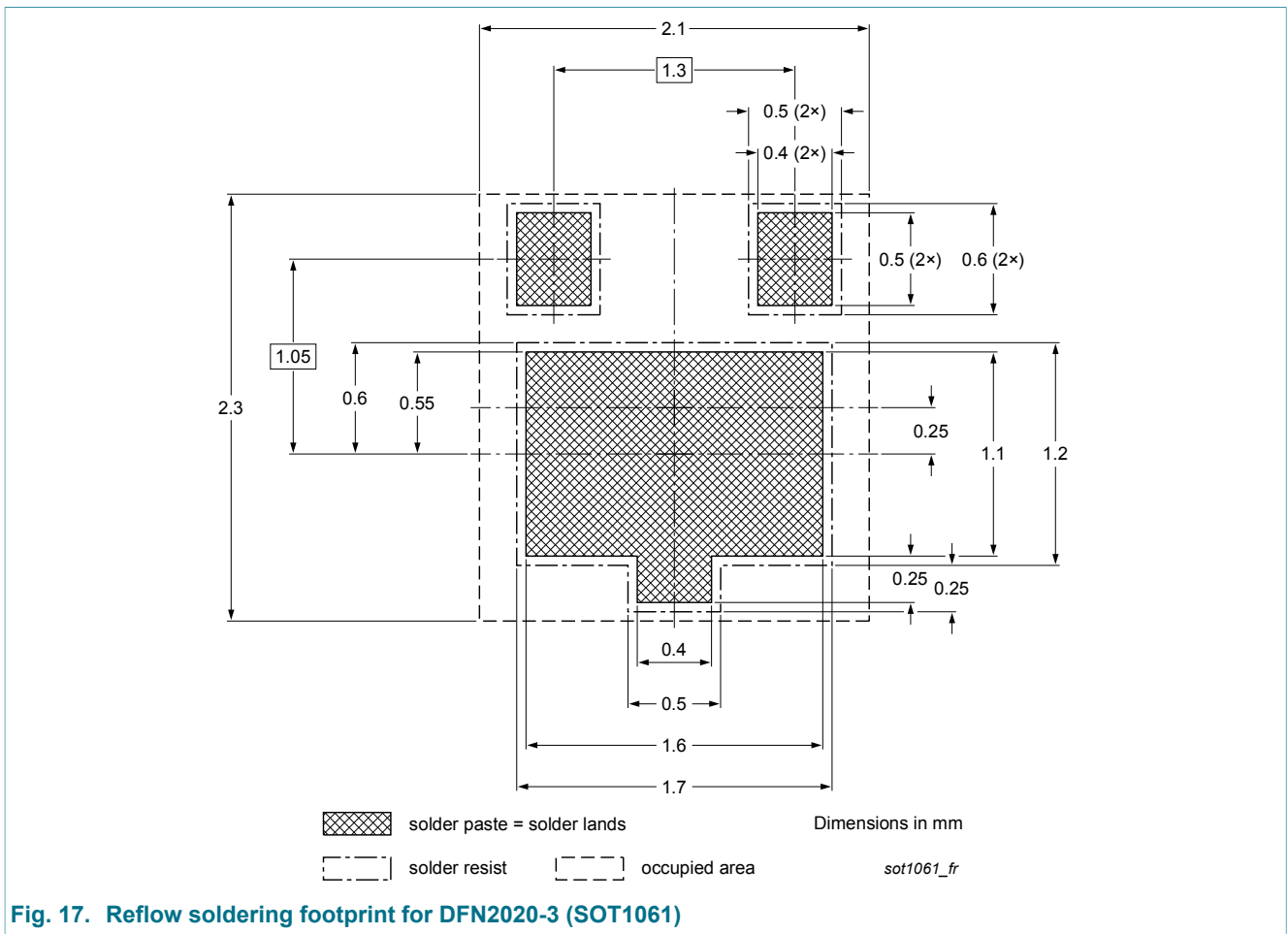


Fig. 17. Reflow soldering footprint for DFN2020-3 (SOT1061)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5330PA v.2	20150407	Product data sheet	-	PBSS5330PA v.1
Modifications:	<ul style="list-style-type: none">Condition V_{CE} changed for parameter I_{CES} in Table 7, Characteristics			
PBSS5330PA v.1	20100419	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 7 April 2015